

TKACHEV, R.A.

Physiopathology of aphasic disorders in vascular diseases of the
brain. Zhur.nevr. i psikh. 55 no.6:422-429 '55. (MLRA 8:8)

1. Institut neurologii AMN SSSR (dir.-prof. N.V. Kononov)
(BRAIN, blood supply
 vasc.disord.causing aphasia)
(APHASIA, etiology and pathogenesis
 brain vasc.dis.)

TKACHEV, R.A.; BRYN, E.S.; PLOTNIKOVA, I.Ya.

Some aspects of restorative therapy in aphasia of vascular origin.
Zhur. nevr. i psikh. 55 no. 12:934-939 '55. (MLRA 9:2)

1. Iz Instituta nevrologii (dir.-prof. N.V. Konovalov) AMN SSSR.
(APHASIA, therapy)

TKACHEV, R.A.

"Prevention of hypertension and atherosclerosis." N.K.Bogolepov,
A.A.Rastvorova. Reviewed by R.A.Tkachev. Zhur.nevr. i psikh. 56
no.5:435 '56. (MIRA 9:8)

(HYPERTENSION)

(BOGOLEPOV, N.K.)

(ARTERIOSCLEROSIS)

(RASTVOROVA, A.A.)

ALEKSANDROVA, L.I., red.; TKACHEV, R.A., red.; GOTOVTSEV, P.I., red.;
BOGACHEVA, Z.I., tekhn.red.

[Problems of the pathogenesis, clinical aspects, and treatment
of neuroses] Voprosy patogeneza, kliniki i lecheniia nevrozov.
Pod red. L.I.Aleksandrovoi i R.A.Tkacheva. Moskva, Gos.izd-vo
med.lit-ry Medgiz, 1958. 204 p. (MIRA 13:1)

1. Akademiya meditsinskikh nauk SSSR, Moscow. Institut nevrologii.
(NEUROSES)

TKACHEV, R.A., kand.med.nauk; ALEKSANDROVA, L.I., kand.med.nauk; PROKHOROVA, E.S.,
kand.med.nauk

Hypertensive cerebral crises. Vest.AMI SSSR 14 no.7:22-29
'59. (MIRA 12:9)

1. Institut nevrologii AMI SSSR.
(BRAIN blood supply)
(HYPERTENSION complications)

TKACHEV, R.A.; ALEKSANDROVA, L.I.; PROKHOROVA, E.S.

Intravenous use of papaverine in acute disorders of brain blood circulation. Sov.med. 23 no.10:106-109 0 '59. (MIRA 13:2)

1. Iz Instituta nevrologii (direktor - deyatvitel'nyy chlen AMN SSSR prof. N.V. Konovalov) AMN SSSR.
(HYPERTENSION compl.)
(BRAIN blood supply)
(PAPAVERINE ther.)

TKACHEV, R.A.: SOLOVYOV, Ye.I.; Moskva, 1965, 1966, 1967.

Problems of heredity in hepatic cerebral dystrophy (Wilson-Donovan's disease). Zhurn. nevrol. i psikh. 65 no.6:821-829 '65.
(MIRA 1b 6)

1. Institut nevrologii (direktor prof. N.V. Kononov) AMN SSSR, Moskva.

DAVIDENKOV, S.N.[deceased], otv. red.; KHONDKARIAN, O.A., zam.
red.; GRASHCHENKOV, N.I., red.; MAN'KOVSKIY, B.N., red.;
MARKOV, D.A., red.; MOROZOV, G.V., red.; TKACHEV, R.A.,
red.; TRIUMFOV, A.V., red.; FEDOTOV, D.D., red.; SHARAPOV,
B.I., red.; SEMENOVA, K.A., red.; BOGDANOVICH, L.A.,
tekhn. red.

[Problems of neuropathology] Problemy nevropatologii;
nauchnye trudy. Moskva, 1963. 323 p. (MIRA 16:8)

1. Vserossiyskoye nauchnoye obshchestvo nevropatologov
i psikiatrov.

(NEUROPATHOLOGY)

TKACHEV, R.A.; ALEKSANDROVA, L.I.; PROKHOROVA, E.S.

Prognosis in hypertensive cerebral crises. Zhur.nevr.i psikh.
62 no.8:1143-1148 Ag '62. (MIRA 15:12)

1. Institut nevrologii (dir. - prof. N.V.Konovalev) AMN SSSR,
Moskva. (CEREBROVASCULAR DISEASE) (HYPERTENSION)

TKACHEV, R. A.; ALEKSANDROVA, L. I.; PROKHOROVA, E. S.

Hypertonic cerebral crises. Nauch. trudy Inst. nevr. AMN SSSR
no.1:35-43 '60. (MIRA 15:7)

1. Institut nevrologii AMN SSSR.

(CEREBROVASCULAR DISEASE) (HYPERTENSION)

SHMIDT, Ye.V., red.; TKACHEV, R.A., red.; KUKUYEV, L.A., red.;
MIRONOVA, A.M., tekh. red.

[Problems in the clinical aspects and pathophysiology of
aphasia] Institut nevrologii. Voprosy kliniki i patofizio-
logii afazii. Pod red. E.V.Shmidta i R.A.Tkacheva. Mo-
skva, Medgiz, 1961. 175 p. (MIRA 15:10)

1. Akademiya meditsinskikh nauk SSSR, Moscow. Institut nevro-
logii.

(APHASIA)

TKACHEV, R.A.; KRYSHOVA, N.A.; BEYN, E.3.

Symposium on asphasia in Bucharest. Vest. AMN SSSR 16 no.6:65-68
'61. (MIRA 15:1)

(APHASIA—CONGRESSES)

TKACHEV, R.Ya.

Inadequacies in the instruction for determining the capacity of
canning and preserving plants. Kons. i ov. prom. 16 no.9:33-35
S '61. (MIRA 14:8)

1. Krasnodarskiy sovmarkhoz.
(Canning industry)

TKACHEV, R.A.

Etiology and pathogenesis of transitory disorders of cerebral
blood circulation. Vest. AMN SSSR 16 no.10:35-41 '61.

(CEREBROVASCULAR DISEASES)

(MIRA 14:11)

TKACHENKO, N.N.; CHIZHOV, S.T.; MESHCHEROV, E.T.; TKACHEV, R.Ya.;
DANILOV, V.P.; KURZINA, I.A., red.; PROKOP'YEVA, L.N.,
tekhn. red.

[Cucumbers] Ogurtsy. [B]N.N.Tkachenko i dr. Moskva, Sel'-
khozizdat, 1963. 205 p. (MIRA 16:5)
(Cucumbers)

TKACHEV, R.Ya.; NAMESTNIKOV, A.F., kand. tekhn. nauk, retsenzont;
YASTREBOV, S.M., inzh., retsenzont; KOVALEVSKAYA, A.I.,
red.; SATAROVA, A.M., tekhn. red.

[Deep-frying of vegetables and fish in canning] Obzharka ovo-
shchei i ryby pri proizvodstve konservov. Moskva, Pishche-
promizdat, 1961. 89 p. (MIRA 15:11)
(Canning and preserving)

TKACHEV, R.Ya.

The workers of the canning industry of Kuban struggle for the fulfillment of the resolutions of the 22d Congress of the CPSU.
Kon.i ov.prom. 17 no.11:4-7 N '62. (MIRA 15:11)

1. Upravleniye promyshlennosti prodovol'stvennykh tovarov
Krasnodarskogo soveta narodnogo khozyaystva.
(Kuban--Canning industry)

TKACHEV, R.Ya.

Shortcomings of a brochure. Kons.i ov.prom. 16 no.3:46-47
Mr '61. (MIRA 14:3)
(Canning and preserving)

TKACHEV, R.Ya.

Brochure "Storage of vegetables in barrels." By D.M. Shilenko,
G.A. Gladkikh, S.A. Belashev. Reviewed by R. IA. Tkachev. Kons.i
ov.prom. 16 no.4:41-42 Ap '61. (MIRA 14:3)
(Vegetables--Storage)
(Shilenko, D.M.)(Gladkikh, G.A.)(Belashev, S.A.)

TKACHEV, R.Ya.

"Home pickling, preserving and marinating" by I.N.Rashchenko.
Reviewed by R.IA.Tkachev. Kons.i ov.prom. 18 no.1:39-40
Ja '63. (MIRA 16:2)
(Canning and preserving) (Rashchenko, I.N.)

TKACHEV, R. Ya.

For a better quality of manuals on the preservation of food at
home. Kons.1 ov. prom. 15 no.6:43-44 Je '60. (MIRA 13:9)
(Food—Preservation)

TKACHEV, Roman Yakovlevich,; SAVZDARG, V.E., red.; GUREVICH, M.M., tekhn. red.

[Processing fruits and vegetables on collective farms] Pererabotka
plodov i ovoshchei v kolkhozakh. Moskva, Gos. izd-vo sel'khoz.
lit-ry, 1958. 174 p. (MIRA 11:11)
(Canning and preserving)

TKACHEV, Roman Yakovlevich; NAMESTNIKOV, A.F., spets.red.;
YERMOKHINA, N.V., red.; KISINA, Ye.I., tekhn. red.

[Equipment for canning green peas] Oborudovanie dlia
konservirovaniia zelenogo goroshka. Moskva, Pishche-
promizdat, 1963. 118 p. (MIRA 16:7)
(Peas, Canned)

TKACHEV, S.

M-17f airplane motor Moskva, Gos. voen. izd-vo, 1936. 105 p. (4C-16962)

TL703.M15T5

TKACHEV, S., brigadir montazhnikov, zasluzhennyy stroitel' RSFSR

Two frames simultaneously. Na stroi.Ros. 3 no.8:3-4 Ag '62.

(MIRA 15:12)

1. Kuznetsovskiy domostroitel'nyy kombinat, Leningrad.
(Leningrad—Construction industry)

TRACHAEV S.D.

TRACHAEV, S. D.

Nekotorye svoistva drevesnykh materialov v razlichnykh napravleniiakh
otnositel'no volokon. (Tekhnika vozdushnogo flota, 1946, no. 7,
p. 15-21, illus., tables, diagrs.)

Title tr.: Some properties of wooden materials with relation to the
direction of the grain.

TL504.T4 1946

SO: Aeronautical Sciences and Aviation in the Soviet Union, Library
of Congress, 1955

SEKT, P.Ye.; TKACHEV, S.F.; LEVIN, S.A.; ALENINA, M.T.; BARANNIK, A.G.

Analyzing the cost indices on the flotation process. Koks 1 khim.
no.9:53-56 '63. (MIRA 16:9)

1. Khar'kovskiy inzhenerno-ekonomicheskij institut.
(Coal preparation plants--Costs)

17

SEKT, P.Ya.; TESLENKO, F.F.; LEVIN, S.A.; TKACHEV, S.F.; ZASHKVARA, V.G.; TOPORKOV, V.Ya.; BELIKOV, A.M.

Location as a factor affecting the economic indices pertaining to the operation of coking coal cleaning plants of the Donets Basin. Koks i khim. no.2:53-56 '60. (MIRA 13:5)

1. Khar'kovskiy inzhenerno-ekonomicheskoy institut (Sekt, Teslenko, Levin, Tkachev). 2. Ukrainskiy nauchno-issledovatel'skiy uglekhi-micheskoy institut (for Zashkvara, Toporkov). 3. Ukrniugleoboga-shcheniye (for Belikov).

(Coal preparation)

TKACHEV, S.F., kand.ekon.nauk

Economic indices of the various stages of coal preparator. Ugol'
Ukr. no.6:38-39 Je '60. (MIRA 13:7)

1. Khar'kovskiy inzhenerno-ekonomicheskii institut.
(Coal preparation--Accounting)

TKACHEV, S.F., kand.ekonom.nauk

Technical and economic effectiveness of the adoption of
pyrite roasting in a fluidized bed. Khim.prom. no.3:
221-222 Ap-My '60. (MIRA 13:8)

1. Khar'kovskiy inzhenerno-ekonomicheskii institut.
(Pyrites) (Fluidization)

TKACHEV, S.F.; TESLENKO, F.F.

Unifying the system of stock taking and accounting at coal-cleaning plants. Koks i khim. no.6:51-54 '60. (MIRA 13:7)

1. Khar'kovskiy inzhenerno-ekonomicheskii institut.
(Coal preparation--Accounting)

SEKT, P.Ya.; TESLENKO, F.F.; BELIKOV, A.M.; TKACHEV, S.F.

Economic aspects of using Donets Basin gas coals for the production of
blast furnace coke. Ugol' 34 no.1:20-23 Ja '59. (MIRA 12:1)

1.Khar'kovskiy inzhenerno-ekonomicheskii institut.
(Donets Basin--Coal) (Coke)

TKACHEV, Sergey Ivanovich

[Development of interfarm cooperation in Kazakhstan] Raz-
vitie mezhkolkhoznykh proizvodstvennykh svyazei v Ka-
zakhstane. Alma-Ata, Kazakhskoe gos.izd-vo, 1963. 98 p.
(MIRA 16:9)
(Kazakhstan--Collective farms--Interfarm cooperation)

TKACHENKO, A.P., inzh.; KRASOVSKIY, Yu.P., inzh.; TKACHEV, S.I., inzh.

Shape of explosion craters and delay intervals in blasting high benches. Shakht. stroi. 8 no.10:8-9 O '64. (MIRA 17:12)

1. Krivorozhskiy gornorudnyy institut (for Tkachenko, Tkachev).
2. Nauchno-issledovatel'skiy gornorudnyy institut, Krivoy Rog (for Krasovskiy).

KITACH, G.M., dotsent, kand. tekhn. nauk; TKACHEV, S.I., gornyy inzh.

Crushing of rocks in short-delay blasting using charges with
air spaces in open-pit mines. Vzryv. delo no.53/10:171-177 '63.
(MIRA 16:8)

1. Krivorozhskiy gornorudnyy institut (for Kitach, Tkachev).
(Krivoy Rog Basin--Blasting)

TRACHEV, S.M., dot sent

Some problems in the kinematics and dynamics of mechanisms
with gaps. Sborn. nauch. trud. Dnepr. inzh.-stroit. inst.
no.21:3 35 '62. (MIRA 17:5)

AAACHEV, S. M.

"On the theory and computation of an elevator with contour scrapers," *Trudy Azovo-Chernomor. in-ta mekhanizatsii sel. khoz-va*, Issue 6, 1948, p. 63-81

SO; U-3850, 16 June 53 (*Letopis 'Zhurnal 'nykh Statey*, No. 5, 1949).

MALKIN, Ya.Z.; SMIRNOV, M.P.; SERGIYENKO, V.Ya.; KOZHEVNIKOVA, G.I.;
KALNIN, Ye.I.; TARKHOV, N.G.; Primali uchastiye: MURSAITOV, Kh.I.;
ABDUGAPAROV, Sh.A.; BOVGUTA, I.D.; TKACHEV, S.P.; FILATOV, N.V.;
SVISTEL'NIKOV, A.M.; PRACHEV, V.N.; SHEYMAN, V.I.; ANTROPOV, A.D.;
SOBOLEV, Ye.D.; POPOVA, N.T.

Industrial testing of a new continuous method of copper removal
from crude lead. TSvet. met. 34 no.3:15-22 Mr '61. (MIRA 14:3)

1. Eksperimental'nyy tsekh Chimbentskogo svintsovogo zavoda (for
Mursaitov, Abdugaparov, Bovguta, Tkachev, Filatov, Svistel'nikov,
Prachev, Sheyman, Antropov, Sobolev, Popova).
(Lead--Metallurgy) (Copper)

LEVIKOV, I.I., inzh.; MARKOV, A.A., inzh.; TKACHEV, S.S., inzh.

"Rules for the technical operation of sinking hoists." Reviewed
by I.I.Levikov, A.A.Markov, S.S.Tkachev. Shakht.stroi. 6
no.4:31-32 Ap '62. (MIRA 15:4)
(Mine hoisting—Safety measures)

TEACHEV, S.Ye.

Local application of penicillin in polyclinical practice in
certain acute inflammatory processes. Sovet.vrach.sborn. no.16:
14-18 Ag '49. (CIME 19:2)

1. Moscow.

TKACHEV, S.E.

Problem of the therapy of hydradenitis. Vest.vener. No.1:56-58 Jan-Feb 51. (CLML 20:6)

1. Candidate Medical Sciences, Lt-Col Medical Corps. 2. Of the Central Red Banner Military Hospital imeni I.V. Mandryk. 3. Comparison of treatment with penicillin and sulfamides.

TKACHEV, S., and N. KAS'IANOV.

Aviatsionnyi motor M-17f; opisanie i rukovodstvo po obsluzhivaniu. Pod red. A. Ustalova. Moskva, Gos. voen. izd-vo, 1936. 105 p., illus., diags.

Title tr.: M-17f aircraft engine; description and maintenance instructions.

TL703.M15T5

SO: Aeronautical Sciences and Aviation in the Soviet Union, Library of Congress, 1955.

TKACHEV, S. E.; NEDOSHIVINA, N. I.

Tissue therapy. Med. sestra, Moskva no. 12:16-18 Dec. 1951.

(CJML 21:3)

1. Tkachev is a Candidate Medical Sciences and Nodoshivina is a senior operating nurse (Moscow).

TKACHEV, Semen Ivanovich; LEPIN, A.E., red.; ONOSHKO, N.G., tekhn.red.

[Speed up the construction of high-quality buildings] Stroit'
bystro i dobrotno! Leningrad, Lenizdat, 1960. 31 p.

(MIRA 13:11)

1. Brigadir kompleksnoy brigady 4-go domostroitel'nogo kombinata
Leningrada (for Tkachev).

(Leningrad--Construction industry)

SEKT, P.Ye.; TESLENKO, F.F.; TKACHEV, S.F.; LEVIN, S.A.; KUZNETSOV, Ye.G.

Technical and economic indices of the operation of the drying units
for dewatering concentrated coals in the Donets Basin. Koks 1 khim.
no.9:47-50 '60. (MIRA 13:9) |

1. Khar'kovskiy inzhenerno-ekonomicheskii institut (for Sekt, Teslenko,
Tkachev, Levin). 2. Stalinskiy sovnarkhoz (for Kuznetsov).
(Donets Basin--Coal--Drying) (Coal preparation)

BUTENKO, Yu.T., inzh.; KRASOVSKIY, Yu.P., inzh.; TKACHEV, S.I., inzh.;
TKACHENKO, A.P., inzh.

Signal for high-speed photography in flame detonation. Met.1
gornorud.prom. no.5:84 S-0 '62. (MIRA 16:1)
(Detonation) (Photography, High-speed)

KOVALEVA, M.F., glav. red.; IGNATOV, S.A., red.; TUSHUNOV, A.V., red.;
TKACHEV, S.I., red.; MATSUK, R.V., red.; NAUMOV, K.M., tekhn.
red.

[Problems of agricultural economics at the present-day stage]
Voprosy ekonomiki sel'skogo khoziaistva na sovremennom etape.
Moskva, Izd-vo VPSH i AON pri TsK KPSS, 1963. 174 p.
(MIRA 16:6)

1. Akademiya obshchestvennykh nauk, Moscow.
(Agriculture—Economic aspects)

Tkachev, S.M., kandidat tekhnicheskikh nauk.

Effect of play on the accurate positioning of a working part of a
mechanism. Sel'khoz mashina no.3:10-12 Mr '57. (MLRA 10:5)
(Machinery)

TKACHEV, S.M., kand.tekhn.nauk, dotsent

Kinematic errors of mechanisms with gaps. Vest.mash, 41 no.11:
42-46 N '61.

(MIRA 14:11)

(Machinery, Kinematics of)

LEVIKOV, I.I., inzh.; MARKOV, A.A., inzh.; TKACHEV, S.S., inzh.

Rules for using hoists in sinking vertical mine shafts. Shakht.
stroï, 5 no.4:33 Ap '61. (MIRA 14:5)
(Shaft sinking) (Mine hoisting—Safety measures)

TRACHEV, S. YE.

USSR/Medicine - Penicillin

Dec 51

"Treatment of Acute Inflammatory Diseases With Penicillin Injections Into the Focus," S. Ye. Trachev, Cand Med Sci

"Vel'dsher i Akusherka" No 12, pp 18-20

Trachev reports on the work done by various authors beside himself on treating many acute inflammatory processes, such as carbuncles, mastitis, paronychia, hidradenitis, and abscesses in various stages of inflammation by injecting, into the focus, doses of 50,000 to 400,000 units of

199788

USSR/Medicine - Penicillin (Contd)

Dec 51

penicillin in combination with novocain. He recommends application of penicillin by this method in such cases in general practice.

199788

TKACHEV, S. Ye.

Penicillin

Rules for the administration of penicillin., Fel'd. i akush., no. 1, 1952
Kandidat Meditsinskikh Nauk

Monthly List of Russian Accessions, Library of Congress, April 1952. UNCLASSIFIED.

TVACHEV, S.Ye.

"Soviet Research on Penicillin Depot in the Organism" Fel'dsher i Akusherka
No 1 Jan 1952 W-22535

TKACHEV, S.Ye.

Penicillin reserve in the organism. Fel'dsher & akush., Moskva No.1:
12-13 Jan 52. (CLML 21:4)

1. Candidate Medical Sciences.

TKACHEV, S. E.

Nurses and Nursing

N. I. Pirogov and the first nurses; 70th anniversary of Pirogov's death.
Med. sestra no. 2, 1952.

Monthly List of Russian Accessions, Library of Congress, April 1952. UNCLASSIFIED.

TEACHOV, S.Ye.

Painless injections. Fel'dsher & akush., Moskva no. 7:38-39 July
1952. (CLML 22:5)

1. Candidate Medical Sciences.

TKACHEV, S.Ye.

Panaritium and its therapy. Vest khir. Moskva 72 no. 5:60-65 Sept-Oct 1952. (CML 23:3)

1. Candidate Medical Sciences.

TEACHEV, S.Ye.

Shock dose penicillin therapy of mastitis. Akush. gin. no. 1:85-86
Jan-Feb 1953. (CIMI 24:2)

1. Candidate Medical Sciences. 2. Moscow.

TKACHEV, S. Ye., kandidat meditsinskikh nauk (Moscow)

Complications in synthonycin therapy. Fel'd. i skush. no. 10:13-14
0 '55. (MLRA 8:12)

(CHLOROMYCETIN)

TEACHEV, S.Ye., kandidat meditsinskikh nauk (Moscow).

Local injection of penicillin. Fel'd.i akush. no.10:30-33 0 '53.

(MIRA 6:10)
(Penicillin)

TKACHEV, S.Ye., kandidat meditsinskikh nauk (Moskva)

Biomycin in medicine. Vol'd. i akush. no.1:16-21 Ja '55. (MLRA 8:3)

(ANTIBIOTICS,
biomycin)

TKACHEV, S.Ye., kandidat meditsinskikh nauk (Moskva)

Twenty-sixth All-Union Congress of Surgeons. Vel'd.i akush. no.5:
47-53 My '55. (MIRA 8:7)

(SURGERY
conf.)

col.
TKACHOV, S.Ye., polkovnik meditsinskoy sluzhby, kandidat meditsinskikh nauk

Treating paronychia. Voen.-med.zhur, no.7:84 J1 '56. (MLRA 9:11)
(FELON (DISEASE))

TKACHEV, S.Ye., kandidat meditsinskikh nauk (Moskva)

Abstract
Treatment of hemorrhoid exacerbations with Shostakovskii's balsam.

Fel'd. i akush. 21 no.3:30-32 Mr '56.

(MLRA 9:7)

(HEMORRHOIDS) (ETHERS)

TKACHEV, S.Ye., kandidat meditsinskikh nauk (Moskva)

On the problem of complications in penicillin therapy. Fel'd. i akush.
21 no.11:12-16 N '56. (MLRA 9:12)

(PENICILLIN)

TKACHEV, S.Ye.

Treating certain inflammations of the anal opening with vinylin
(Shostakovskii's balsam). Novkhir.arkh. no.1:69 Ja-F '58 (MIRA 11:11)

1. Vtoraya moskovskaya tsentral'naya poliklinika.
(ANUS--DISEASES)
(ETHERS)

TKACHEV, S.Ye., polkovnik med. sluzhby, kand.med.nauk

Blind suture in treating suppurative atheromas and other inflammations.
Voen.med.shur. no.3: Mr '57. (MIRA 11:3)
(SKIN--TUMORS) (SUTURES)

TKACHEV, S.Ye.

Topographic administration of penicillin. Vel'dsher & akush. no.10:
30-33 Oct 1953. (CIML 25:4)

1. Candidate Medical Sciences. 2. Moscow.

TKACHEV, S.Ye., kandidat meditsinskikh nauk (Moskva)

Testing sensitivity to antibiotics. Klin. med. 35 no.2:152-153
P '57 (MLRA 10:4)

(ANTIBIOTICS, off.
sensitivity, determ., skin test)

TRACHEV, T.Ya., prof.

Increasing necessity. Sov.zdrav. 16 no.12:46-47 D '57. (MIRA 11:1)

1. Iz Voronezhskogo meditsinskogo instituta (dir. - prof. N.I. Odnoratov)

(PUBLIC HEALTH, educ.

in Russia, recommendations for change (Rus))

TKACHEV, T.Ya., prof.

Men of science and medicine from Nizhniy Novgorod." Reviewed by
T.IA. Tkachev. Sov,zdrav. 18 no,11:59-60 '59. (MIRA 13:3)
(GORKIY--SCIENTISTS)

TKACHEV, T.Ya., prof. (Voronezh).

Problems in teaching medical history. Sov. zdrav. 18 no.2:34-38 '59.
(HISTORY, MEDICAL, educ. (MIRA 12:1)
(Rus))

TKACHEV, T.Ya., prof. (Voronezh)

Scientific-atheistic propaganda in a higher medical school. Sov.
zdrav. 20 no.1:46-49 '61. (MIRA 14:5)
(MEDICINE—STUDY AND TEACHING) (RELIGION)

TKACHEV, T.Ya.

~~TKACHEV, T.Ya.~~
Z. P. Solov'ev, 75th anniversary of birth. Sovet. med. no.11:35-36
Nov 1951. (CML 21:2)

1. Professor. 2. Voronezh.

14(1)

SOV/66-59-3-29/31

AUTHOR: Tkachev, V.

TITLE: Heat Transfer in Wire and Tube Condensers /From foreign publications/

PERIODICAL: Kholodil'naya tekhnika, 1959, Nr 3, pp 75 - 76 (USSR)

ABSTRACT: Issues Nr 3 and Nr 9 of the Journal "Refrigerating Engineering", 1957, contained articles pertaining to wire and tube condensers. The article discusses the design, applications and merits of this type of condensers; it also develops formulae for calculating heat transfer. There are: 1 graph, 1 diagram and 4 references, of which 2 are Soviet and 2 English.

Card 1/1

TKACHEV, V.

85-58-6-30/43

AUTHORS: Tkachev, V., Vartanov, V., Vasilyan, I., Lagunov, V.,
Lobzhanidze, Z., Guruli, M. (Tbilisi)

TITLE: Tbilisi Model-airplane Builders Need a Field for Flying Cord-
controlled Models (Tbilisskim aviamodelistam nuzhen kortodrom)

PERIODICAL: Kryl'ya rodiny, 1958, Nr 6, p 24 (USSR)

ABSTRACT: The authors urge the construction of a field for flying
cord-controlled airplane models in Tbilisi.

1. Airplanes—Model building

Card 1/1

GRIDNEV, S.; TKACHEV, V.

Develop equipment for open electric power stations. NTO 4
no.8:32-34 Ag '62. (MIRA 15:8)

1. Direktor Rostovskogo otdeleniya Vsesoyuznogo gosudarstvennogo
proyektnogo instituta stroitel'stva elektrostantsiy, predsedatel'
soveta Nauchno-tekhnicheskogo obshchestva energeticheskoy promy-
shlennosti (for Gridnev). 2. Glavnyy inzh. Rostovskogo
otdeleniya Vsesoyuznogo gosudarstvennogo proyektnogo instituta
stroitel'stva elektrostantsiy, zamestitel' predsedatelya soveta
Nauchno-tekhnicheskogo obshchestva energeticheskoy promyshlennosti
(for Tkachev).

(Electric power plants)

88016

S/170/60/003/012/013/015
B019/B056

9,3250 (1143,1154,1331)

AUTHORS: Nekrashevich, I. G., Geller, I. Kh., Tkachev, V. D.
TITLE: Galvanic Effects in Selenium Rectifier Elements
PERIODICAL: Inzhenerno-fizicheskiy zhurnal, 1960, Vol. 3, No. 12,
pp. 114-118

TEXT: The authors investigated the effect produced by moisture upon selenium rectifiers. In several experimental series, the behavior of the elements in moist and dry air was investigated. The results indicate that by the air moisture in the elements a galvanic EMF is formed, which is produced by the forming of galvanic couples between the lower and the upper electrode and between selenium and the upper electrode. These two couples act within a closed circle of a rectifier element in an opposite direction. These galvanic effects and their changes with a change of the moisture penetrating into the element from outside are considered to be causes of the fluctuations of the return current and of the destruction of selenium rectifier elements. There are 3 figures and 2 tables. X

Card 1/2

88016

Galvanic Effects in Selenium
Rectifier Elements

S/170/60/003/012/013/015
B019/B056

ASSOCIATION: Belorusskiy gosudarstvennyy universitet im. V. I. Lenina,
g. Minsk (Belorussian State University imeni V. I. Lenin,
Minsk)

SUBMITTED: January 22, 1960

X

Card 2/2

TKACHEV, V.D.; LOGINOV, A.S.

Gases in the blood in cirrhosis of the liver and chronic hepatitis.
Terap.arkh. no.6:17-21 '62. (MIRA 15:9)

1. Iz Instituta terapii (dir. - deystvitel'nyy chlen AMN SSSR
prof. A.L. Myasnikov) AMN SSSR.
(LIVER--DISEASES) (BLOOD, GASES IN)

TKACHEV, V.D.

Disorders of blood coagulation in liver diseases.
Akt.vop.pat.pech. no.3:136-146 '65.

(MIRA 18:11)

: 44168

S/181/62/004/012/015/052
B104/B102

24.7500

AUTHORS:

Vavilov, V.S., Plotnikov, A.F., and Tkachev, V.D.

TITLE:

Investigating structural defects in silicon single crystals by reference to the photoconductivity

PERIODICAL:

Fizika tverdogo tela, v. 4, no. 12, 1962, 3446-3454

TEXT: The photoconductivity spectra of p- and n-type Si single crystals with different oxygen, boron, and phosphorus concentrations, irradiated by electrons (~1 Mev) from the electrostatic generator of the Laboratory of the FIAN at 100 and 300°K, were investigated with a recording spectrometer designed on the basis of the MKC-12 (IKS-12) monochromator. The specimens were plates (15.2.5.0.8 mm) with palladium contacts (p-type specimens) or with zinc contacts (n-type specimens). Results: Irradiation leads to the appearance of a large number of discrete levels in the forbidden band. The dependence of the shape of the photoconductivity spectrum on the position of the Fermi level, which is related to the excitation of electrons on the different levels, shows

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Investigating structural defects ...

S/181/62/004/012/015/052
B104/B102

that all levels (Fig. 11) can be related to defects. The higher sensitivity of photoelectric measurements as compared with electric measurements made it possible to prove the existence of a series of centers with different ionization energies. In Si single crystals, irradiation by neutrons produces the same defects as by electrons. The radiation defects which determine the photoconductivity spectrum of Si in the range of 2 to 6 μ , are not Frenkel' defects. Irradiations at 100°K showed that at room temperature not only simple Frenkel' defects exist, but also associations of these with other types of defects. This makes it possible to study how such associations are formed and to determine the characteristics of defect diffusion. Electrically active impurities (Cu, Au) with concentrations of 10^{11} to 10^{12} cm^{-3} could be identified by studying photoconductivity spectra. There are 12 figures.

ASSOCIATION: Fizicheskiy institut im. P.N. Lebedeva AN SSSR Moskva.
(Physics Institute imeni P.N. Lebedev AS USSR, Moscow)

SUBMITTED: July 6, 1962

Card 2/3

44177

9.4177
24.2600

S/181/62/004/012/031/052
B125/B102

AUTHORS: Plotnikov, A. F., Tkachev, V. D., and Vavilov, V. S.

TITLE: The photoconductivity spectra of monocrystals related with residual impurities

PERIODICAL: Fizika tverdogo tela, v. 4, no. 12, 1962, 3575-3577

TEXT: The photoconductivity spectra of silicon monocrystals ($\approx 1000 \text{ ohm}\cdot\text{cm}$) were examined at 100°K at constant and alternating excitation (modulating frequency of the light 9 cps). The crystals were either produced by zone melting in vacuo or were grown in quartz crucibles. The measuring apparatus, described by A. F. Plotnikov et al. (PTE, 3, 1962) recorded variations in the dark conductivity up to 10^{-8} . The λ -dependences of the relative change $\Delta\sigma/\sigma$ in the photoconductivity of p-type silicon monocrystals of 500 and 75 $\text{ohm}\cdot\text{cm}$, have the same step-like form. I is the intensity of the exciting light. The photoconductivity beyond 3.2μ may be related with the known donor level of gold which lies 0.35 eV above the v-band. This level is due to centers whose concentrations vary between 10^{10} and 10^{11} cm^{-3} . This concentration of monocrystals produced in quartz

Card 1/3 ① 5/120/62/000/003/042/048

The photoconductivity spectra ...

S/181/62/004/012/031/052
B125/B102

dishes is higher by one order of magnitude than that of silicon produced by vertical zone melting in vacuo. The level at 1.8μ corresponds to bipolar excitation, the level at 2.2μ corresponds to the acceptor level lying 0.54 ev below the bottom of the c-band and the level 2.8μ arises from bipolar excitation by the copper level $E_v + 0.49 \text{ ev}$. In the latter case, minority carriers (electrons) are excited by double optical transitions to the conduction band. The level in the region 2.3μ of the λ -dependence of $\Delta\sigma/\sigma I$ is evidently due to electron excitation from the gold level $E_c - 0.54 \text{ ev}$ to the conduction band. The broader level below 2μ might be due to bipolar electron excitation through 2 levels. The shape of the spectral curves of the photoconductivity of p-type silicon monocrystals (doped with gold up to $5 \cdot 10^{15} \text{ cm}^{-3}$) confirms the above assumption that the impurity photoconductivity in unalloyed Si crystals is caused by gold atoms. In Si monocrystals produced by zone melting in vacuo without any crucible the gold concentration is found to be $10^{10} - 10^{11} \text{ cm}^{-3}$ and the copper concentration $10^{11} - 10^{12} \text{ cm}^{-3}$. In Si monocrystals grown in quartz crucibles or by vertical zone melting the

Card 2/3

The photoconductivity spectra ...

S/181/62/004/012/031/052
B125/B102

residual impurities, copper and gold, produce local centers with deep levels in the forbidden bands. There are 3 figures.

ASSOCIATION: Fizicheskiy institut im. P. N. Lebedeva AN SSSR, Moskva
(Physics Institute imeni P. N. Lebedev AS USSR, Moscow)

SUBMITTED: July 10, 1962

Card 3/3

L 15556-63

Pz-4 AT/IJP(C)

EWI(1)/EWG(k)/EWI(m)/BDS/EEC(b)-2

AFFTC/ASD/ESD-3

ACCESSION NR: AP3003876

S/0181/63/005/007/1826/1829

AUTHORS: Tkachev, V. D.; Plotnikov, A. F.; Vavilov, V. S.

TITLE: Spectra of photoconductivity in n-type silica bombarded with high-speed electrons

SOURCE: Fizika tverdogo tela, v. 5, no. 7, 1963, 1826-1829

TOPIC TAGS: photoconductivity, silica, n-type, electron, high-speed electron, conduction band, valence band, forbidden band, center, defect

ABSTRACT: The photoconductivity of n-type silica was studied by means of the setup described by A. F. Plotnikov, V. S. Vavilov, and B. D. Kopylovskiy (PTE, No. 3, 183, 1962). The spectra were investigated with oscillating (modulation frequency of 9 cycles) and steady excitation. The samples were plates cut from single crystals and had contacts attached at the ends. The contacts were Pd and Zn, deposited electrolytically. The bombardment was effected with electrons of 1 Mev. The temperature of the samples during bombardment did not exceed 25-30C, and measurements were made at a temperature near 100K. From the measurements of photoconductivity the authors diagrammed the positions of energy levels in the

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L 15556-63

ACCESSION NR: AP3003876

forbidden band. This diagram is shown in Fig. 1 (see Enclosure 1). The results, like data on bombardment of p-type silica with electrons and neutrons, attest to a "set" of several centers, the nature of most being as yet unexplained. The "radiation" origin of centers with levels at $E_c - 0.16$, $E_c - 0.40$, $E_v + 0.54$, and $E_v + 0.45$ ev is not questioned. These levels are starred in Fig. 1. It is possible that some of the levels are initially present in the material, not developing anew but merely appearing because of the capture of equilibrium carriers by defects and because of favorable conditions for measuring photoconductivity in bombarded silica at low temperatures. "The authors express their sincere thanks to G. N. Galkin, V. M. Malovetskaya, and V. I. Brovkinaya for valuable advice and critical remarks and to Yo. M. Divil'kovskaya (deceased) for aid in the work." Orig. art. has: 6 figures.

ASSOCIATION: Fizicheskiy institut im. P. N. Lebedeva AN SSSR, Moscow (Physical Institute, Academy of Sciences, SSSR)

SUBMITTED: 30Jan63

DATE ACQ: 15Aug63

ENCL: 01

SUB CODE: PH

NO REF SOV: 005

OTHER: 002

Card 2/3

TKACHEV, V.D.; PLOTNIKOV, A.F.; VAVILOV, V.S.

Nature of local centers with deep-seated levels in silicon
irradiated by fast electrons. Fiz. tver. tela 5 no.11:3188-3194
N '63. (MIRA 16:12)

1. Fizicheskii institut imeni Lebedeva AN SSSR, Moskva.

VAVILOV, V. S.; TKACHEV, V. D.; SAVCHENKO, A. N.

"On the nature of local centers with deep energy levels in silicon irradiated by fast electrons."

report submitted for Symp on Radiation Damage in Semiconductors, Royaumont, France, 16-18 Jul 64.

ACCESSION NR: APh033646

S/0250/64/008/003/0147/0149

AUTHORS: Sevchenko, A. N.; Tkachev, V. D.

TITLE: Kinetics of photoconductivity in n-type silicon single crystals irradiated by high speed electrons

SOURCE: AN BSSR. Doklady*, v. 8, no. 3, 1964, 147-149

TOPIC TAGS: impurity photoconductivity, silicon single crystal, electron beam, conduction zone, electron concentration, relaxation curve

ABSTRACT: The kinetics of impurity photoconductivity in n-type silicon single crystals, irradiated by 1 Mev electron beam, was studied. The investigated kinetics were connected with electron transitions of $E_c = 0.16, 0.26, 0.29$, and 0.40 eV centers in the conduction zone. All measurements were made at 80K. In the analysis it is assumed that thermal exchange between the investigated levels and zones is negligible. The solution of the kinetic equation is then given in the form of

$$\Delta n_s = \Delta n_{cr} \left[1 - \exp\left(-\frac{t}{\tau_s}\right) \right]$$

and
Card

1/2

ACCESSION NR: AP4033646

$$\Delta n_c = \Delta n_{cr} \exp\left(-\frac{t}{\tau_c}\right)$$

where Δn_H - increase in electron concentration and τ_H - growth constant. Typical relaxation curves are given for energy level $E_c = 0.16$ eV, obtained by irradiating the specimen to increase the Fermi level slightly higher than the given center energy level E_c . From these measurements electron capture cross sections were determined for each level to an accuracy of 70%. Orig. art. has: 7 formulas and 2 figures.

ASSOCIATION: Belorusskiy gosudarstvennyy universitet im. V. I. Lenina (Belorussian State University)

SUBMITTED: 26Dec63

SUB CODE: SS

NO REF SOV: 004

ENCL: 00

OTHER: 000

Card 2/2

ACCESSION NR: AP4039327

S/0250/64/008/004/0223/0225

AUTHORS: Tkachev, V. D.; Sevchenko, A. N.; Lugakov, P. F.

TITLE: Capture of minority current carrier in n-type silicon irradiated by fast electrons

SOURCE: AN BSSR. Doklady*, v. 8, no. 4, 1964, 223-225

TOPIC TAGS: minority current carrier, silicon single crystal, hole type, photoconductivity, hole capture, adhesion center, infrared radiation

ABSTRACT: The process of minority current carrier adhesion in n-type silicon single crystals has been studied under high speed electron beam radiation (1 Mev). The monocrystal was obtained by the method of vertical melt zone in vacuum, containing not more than 5×10^6 oxygen atoms per 1 cm^3 as well as by growing it in a quartz tube containing 10^{18} oxygen atoms per cc. Nonequilibrium carriers were injected by means of light pulses. In the case of the quartz grown single crystal, hole capture was noticed clearly at low temperatures (80K) under electron bombardment. The photoconductivity of this crystal is represented graphically as a function of radiation time with an integrated electron current of 1.2×10^{17} electrons/cm² (see Fig. 1 on the Enclosure). The figure shows that after switching

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ACCESSION NR: AP4039327

on the light the conductivity increases sharply because of the generation of nonequilibrium carriers with time durations of the order of hole lifetimes in the monocrystal. The nonlinear rise $\Delta \sigma_2$ may be explained by photo-hole capture centers filled with electrons after switching on the light. The energy locations of adhesion centers are determined from the photoconductivity changes connected with infrared radiation absorption. "The authors are deeply grateful to V. S. Vavilov and A. F. Plotnikov for their many valuable remarks, and to A. G. Litvinko and M. T. Lappo for their help." Orig. art. has: 2 figures.

ASSOCIATION: Belorusskiy gosudarstvennyy universitet im. V. I. Lenina (Belorussian State University)

SUBMITTED: 25Dec63

DATE ACQ: 09Jun64

ENCL: 01

SUB CODE: SS

NO REF SOV: 001

OTHER: 003

Card 2/3

I. 4974-66 EWT(1)/EWT(m)/EPF(c)/EPF(n)-2/T/EWP(t)/EWP(b)/EWA(c) IJP(c) JD/GG
 ACC NR: AP5027426 44,55 SOURCE CODE: UR/0181/65/007/011/3410/3412

AUTHOR: Yukhnovich, A. V.; Tkachev, V. D. 44,55

ORG: Belorussian State University im. V. I. Lenin, Minsk (Belorusskiy gosudarstvennyy universitet) 44,55 65 23

TITLE: Radiative recombination in silicon containing radiative structure dislocations 21 44,55

SOURCE: Fizika tverdogo tela, v. 7, no. 11, 1965, 3410-3412

TOPIC TAGS: electron recombination, recombination emission, recombination radiation, crystal dislocation 21, 44,55

ABSTRACT: An investigation was made of the recombination mechanism associated with the structure dislocations of the lattice over deep energy levels in the forbidden band of silicon. To produce radiative dislocations, the specimens were irradiated with gamma-quanta from a Co^{60} source with an integrated dose of 10^{16} — 10^{20} cm^{-2} . Nonequilibrium carriers were excited by electric injection through the diffusive p-n transition. The initial material had a resistivity of 2 ohm·cm. The emission was detected with a cooled PbS detector and analyzed with an IKS-12¹ monochromator. In addition to the emission band close to 0.96 ev, a band was observed with a width about 0.1 ev. It had two emission lines with maxima of 0.478 and 0.488 ev and half-widths of 5×10^{-3} and 2.5×10^{-3} ev, respectively. The width of these lines and the

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L 4974-66

ACC NR: AP5027426

position of their maxima did not change significantly with variations of the specimen's temperature in a range from 65 to 130K. The form of the spectrum and temperature dependences of the intensity were similar for n- and p-type specimens. The width of 0.478 and 0.488 eV emission lines was considerably smaller than the value of kT at the temperature of the experiment, which is attributed to the localization of the initial and end states of the electron and the hole, which participate in the corresponding transitions. It was assumed that these lines appear at a radiative capture of one of the carriers from an excited state into the ground state of a defect which is located at the middle of the forbidden zone of silicon. The "background" intensity decreased when the temperature was reduced from 100 to 65K. In this temperature range, it appeared that the energy was "pumped over" from a nonstructural background into narrow lines. The assumption that the whole emission of the band initiates in one center was confirmed experimentally in investigations of the dependence of the intensity of separate band components on the integral irradiation dose. Orig. art. has: 2 figures.

[JA]

SUB CODE: 6C, 55, NPSUBM DATE: 13May65/ ORIG REF: 004/ OTH REF: 002/ ATD PRESS:

4138

OC

Card 2/2

10047-00 ENL(1) LJP(5) AI

ACC NR: AP6002391

SOURCE CODE: UR/0250/65/009/012/0801/0803

AUTHOR: Sevchenko, A. N.; Tkachev, V. D.; Lugakov, P. F.

ORG: Belorussian State University (Belorusskiy gosudarstvennyy universitet)

TITLE: Bipolar mechanism of exciting impurity-type photoconductance

SOURCE: AN BSSR. Doklady, v. 9, no. 12, 1965, 801-803

TOPIC TAGS: photoconductance, photoconductance excitation, semiconductor

ABSTRACT: Results are briefly reported of an experimental investigation of the bipolar excitation of photoconductance by means of double optical transitions of electrons through local energy levels which were introduced into the Si forbidden band by radiational structure disturbances. Experiments were conducted to prove the possibility of the bipolar excitation through the center $E_v + 0.34$ eV ($E_c - 0.78$ eV). A plot is presented of photoconductance damping after the cessation of excitation (by 0.78-eV quanta) of an n-Si specimen irradiated by a 2×10^{16} -el/cm² beam. Also, curves showing the effect of the exciting-light wavelength (1-4 mμ) on the electron concentration in the conduction band are given; the integral electron beam was 7×10^{16} ; the curves were measured at liquid-nitrogen temperature. Orig. art. has: 2 figures.

SUB CODE: 20 / SUBM DATE: 14Jun65 / ORIG REF: 003

Card 1/1

L 23147-66 EWT(m)/T/EWP(t) IJP(c) JD
ACC NR: AP6006847 SOURCE CODE: UR/0181/66/008/002/0564/0565

AUTHOR: Yukhnevich, A. V.; Tkachev, V. D.; Lomako, V. M.

ORG: Belorussian State University im. V. I. Lenin, Minsk (Belorusskiy gosudarstvennyy universitet)

TITLE: Extrinsic radiative recombination in single crystals of silicon

SOURCE: Fizika tverdogo tela, v. 8, no. 2, 1966, 564-565

TOPIC TAGS: radiative recombination, silicon, single crystal, crystal theory, impurity band

ABSTRACT: The authors attempt to explain the mechanism responsible for impurity recombination by studying the recombination radiation which is produced when non-equilibrium carriers are captured by deep levels in the forbidden band which are the result of residual chemical impurities and other imperfections in the crystal lattice. Excitation was produced by electrical injection through a diffused pn junction. The radiation was recorded by a system including a monochromator, lead sulfide receiver and narrow band amplifier. In addition to the natural emission band, the specimens showed an emission band in the impurity region with a maximum at 1.47 μ . The position of this maximum is independent of the conductivity type, resisti-

Card 1/2

L 23147-66

ACC NR: AP6006847

vity and previous history of the specimen. The intensities of the natural and impurity bands differ noticeably from specimen to specimen for various current densities and temperatures. No correlation was found between the dislocation concentration in the single crystals and the nature of the impurity radiation. The nature of the emitters responsible for this impurity radiation may be determined by studying recombination radiation in crystals specially doped with various chemical impurities. The authors are grateful to Z. M. Afanas'yev and M. V. Bortnik for assistance with the experiment. Orig. art. has: 1 figure. 2

SUB CODE: 20/

SUBM DATE: 25Jul65/

ORIG REF: 001/

OTH REF: 001

Card 2/2 VUR

L 28001-66 EPF(n)-2/EWT(1)/EWT(m)/EWP(t)/ETI IJP(c) GG/JD
 ACC NR: AP6012496 SOURCE CODE: UR/0181/66/008/004/1264/1265
 59
 58
 B

AUTHOR: Yukhnevich, A. V.; Tkachev, V. D.
 ORG: Belorussian State University im. V. I. Lenin, Minsk (Belorusskiy gosudarstvennyy universitet)

TITLE: Optical analog of the Mossbauer effect in silicon 27

SOURCE: Fizika tverdogo tela, v. 8, no. 4, 1966, 1264-1265

TOPIC TAGS: silicon, Mossbauer effect, recombination radiation, crystal defect, radiation damage, single crystal

ABSTRACT: This is a continuation of earlier studies of the recombination radiation of single-crystal silicon containing stable radiation defects, where bands of impurity radiation with characteristic lines having a width smaller than kT were observed (FIT v. 7, 3410, 1965). In the present investigation the authors observed additional emission bands occurring in silicon during the course of annealing of radiation defects. Nonequilibrium carriers were produced in n-type silicon with resistivity 4.5 ohm-cm by electric injection through a diffusion p-n junction. The recombination radiation was analyzed with a measurement setup described earlier. The samples were irradiated with a dose of 5×10^{18} photons/cm² γ-rays from Co⁶⁰ at room temperature. The annealing was in vacuum of 10^{-4} mm Hg. Five different bands were observed. They appeared and disappeared simultaneously during the course of isochronous annealing. Two of these were observed in the earlier investigations. Comparison of the structure of the ob-

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